

Master Thesis

**Evaluation, design and realisation of a
Riemann Pump for the frequency
range of 0..6 GHz for 5G mobile
communication**

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Declaration

I hereby declare that this thesis is my own work and effort and that all sources cited or quoted are indicated and acknowledged by means of a comprehensive list of references.

Freiburg, 30.04.2016

Markus Weiß

Abstract

Agenda

1. literature survey
2. adaption of push-pull concept from Maksimovic (Talk at Fraunhofer IAF 06/2015)
3. GaN25 GaN (gallium nitride) parameter simulation [S-parameter, ON/OFF switching voltage]
4. determine load impedance [input of PPA - GaN25 HEMT (high electron mobility transistor)]
5. determine dimension of transistors
6. tuning schematic parameter for optimal simulation (special freq?)
7. enhancement/extension of 1-bit push-pull to 3-bit push-pull stage
8. digital input control voltage
9. determine eight slopes of the current sources in schematic 3-bit resolution
10. Riemanncode generation with MatLab; minimizing error
11. control schematic with theoretical input [Riemanncode]

Problems

1. frequency dependent load impedance
2. absence of p-type transistor makes it hard to efficiently switch the high side transistor in the Gbps range
3. the heat spreading on the chip and substrate is critical
4. energy consumption may be very high (mainly switching losses)
5. the absence of accurate current sources makes it very hard to get a defined slope for the switching transistors.
6. theoretical slope generation very inaccurate
7. theoretical slope generation via shorted load ($R = 1 \Omega$)
8. \rightarrow *slopes ambiguous?*

9. → *riemanncode generation not possible?*

questions

1. mmW band much higher BW, Datarate, Spectrum - why use the old fashioned frequency bands from DC to 6GHz instead of using a couple of GHz?
 - Signal generation is done for the bandwidth of 0..6 GHz, after that it could be mixed up to higher frequency bands like 47 GHz to 53 GHz
2. trade off between BW and losses
 - higher bandwidth means higher switching speed means higher losses due to the fact that the losses increase linear with the switching speed
 - higher frequencies means higher attenuation (e.g. weather condition, like rain)

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List of abbreviations

ADS	Advanced Design System
DAC	digital-to-analog converter
GaN	gallium nitride
HEMT	high electron mobility transistor
IAF	Fraunhofer-Institut für Angewandte Festkörperphysik
LTE	Long-Term Evolution
OSR	oversampling ratio

List of symbols

f frequency

1. Introduction

A brief summary of the contents of the thesis, including what was done and, in general terms, what was achieved. Two pages maximum

*Explanation of why you had to do what you did. At the end of this section, you should summarize your most important results in one to two pages, including your best measurement result. **Description of the task.***

Mobile communication became a major part of our daily life. With the release of the fourth mobile communication standard LTE (Long-Term Evolution), over seventy 70 'Kraftwerke' (-> EPCOS Ordner gucken !! WICHTIG) In our every day life applications such as Instagramm, Whatsapp, facebook and Snapchat are dealing with very high data transfer rates. The industry also handles a very big amount of data. Real time trading at a stock exchange market is crucial, so the industry tries to reach this with the help of RF mobile communication. The data rate is increasing exponentially up to the year 2020. Todays hardware architectures can not handle this amount of data. In the next generation, the fifth, of mobile communication different concepts are needed to deal with this high data rate. In the next generation new hardware architecture are needed. This new concepts are based on the idea of a full software radio. The concept is basically to bring the digital domain as close as possible to the RF Front-End. Therefore the filter, mixer and computation would be much faster, more accurate and less complex.

In Chapter two some fundamentals are explain to get a better understanding of the work. Chapter three explains the design workflow to get to an working principle and a schematic. Chapter four evaluates the principle and after a successful simulation the layout is done in chapter five. after designing and layouting the schematic lastly the measurements are taken. in the end the results are discussed.

5G will be the gamechanger for autonomous driving. low latency (nearly realtime) and super high speed networks. Ten years ago the most shared thing was text, then it becomes pictures and nowadays it is video. But this is not the end of the line, the next step would be a 360 degree angle camera, 3 dimensional, high resolution live stream a la virtual reality. This would mean the next mobile communication standard, 5G, is an enhancement for high data rate and bandwidth and of course the low latency, near to real time transmission. Another topic will be the voice controlled everything, keyword IoT. The smartphone will be overcome with another gadget, most likely voice controlled. This voice control creates a lot more data than tipping it into the keyboard of a smart-

phone. 5G also means to connect the world, so Mark Zuckerberg. The next standard should be more efficient, cheaper and therefore it should be affordable for every country. Also it could be possible to cover those countries via satellite. sciencetogo Ambacher

Sendeleistung der Basisstation betraegt 20W. Elektronische Komponenten brauchen aber mehrere tausend Watt (kW) um die Informationen an den Empfaenger zu senden. PA am wichtigsten, hohe leistung, geringe Leistungsaufnahme, hohe frequenz. mehr als 70.000 Basisstationen deutschlandweit, Energieverbrauch/Jahr: 2 Mrd kWh entspricht der jaehrlich eingespeisten Energie eines kleinen Kohlekraftwerks. Energiebedarf weltweit werden etwa 70 Kernkraftwerke noetig. Mobilfunknutzer steigt: 2020 4.6 Mrd Nutzer, 2020 1800 Billionen Bytes, technisch energieeffiziente loesungen noetig ohne umwelt zu belasten. 5G bis 2020. 1 Mrd bit/s 10mal soviel wie LTE. Extrem schnelle und energieeffiziente power amplifier. Avlanche breakdown! UMTS Basisstation: 20km, LTE mehr Daten weniger Reichweite, hoehere Frequenz: 5km, Reichweite muss in der naechsten Generation auch erhalten bleiben, also viel Leistung auf noch hoeheren Frequenzen. Silizium schafft die Leistung nicht, das Silizium wuerde viel zu heiss, deswegen III-V Verbindungshalbleiter. 3000 Watt Energieaufnahme um mit fuenf antennen jeweils 20 Watt im Umkreis von 20km fuer 600 Telefonate gleichzeitig zu verteilen. Filme, Musik, Stream -> Datenrate und zwar 10 bis 100-fach hoehere Datenrate als LTE. 100 Milliarden Geraete sollen gleichzeitig ansprechbar sein WELTWEIT (Computer, PDA, Auto, Smartphone etc.). Latenzzeiten von unter 1 ms!! Fast Echtzeit, Maschinenkommunikation !! Maschinen sind sehr empfindlich und muessen zu jedem Zeitpunkt wissen wo sie stehen. Energieverbrauch soll um ein tausendstel pro bit gesenkt werden. (insgesamt soll der stromverbrauch um 90 prozent verringert werden) GaAs wird vollstaendig verschwinden, sowohl mobil als auch basisstationen werden auf GaN umruesten muessen. Neue Geraete werden notwendig, 5G wird nicht kompatibel sein mit den alten Standards.

2. Research and Development of 5G mobile communication

An optic survey of the state-of-the-art with extensive references. State of the art of the next generation of mobile communication. Mobile Congress 2016 in Barcelona, Huawei & Telekom present a first data link in 73 GHz with a few Gbps.

First attempts on a digital to analog converter for the frequency range based on the concept of a charge pump, were designed by french people Veyrac et. al

Mark Zuckerberg hold a speech about fifth generation of mobile communication. The goal is to provide and deliver internet to everyone in every country.

3. Fundamentals-Theory for this approach to reach 5G

Presentation of the theoretical basis required for an understanding of your work. Do not begin with Newton's laws or Maxwell's equations: imagine that the reader is a competent engineering professor, but not necessarily in your field of expertise. Do not bother to discuss any theory that you do not employ in later sections. In the following some fundamentals are described shortly.

3.1. Concept of Software-defined radio

The concept of software-defined radio is adapted to deal with the old problems of mobile communication. The idea is to bring the digital domain as close as possible to the RF front end. The reason is digital filtering, data processing is more efficient, easier, less complex, has less cost, and so on. The main problem of this approach is the energy consumption based on an inefficient ADC/DAC. However the concept is very helpful for future designs of a digital front end. The Software-defined radio has the advantage, that it is adaptive for future software changes. the hardware is still the same, only the firmware has to be upgraded. a broad spectrum of signal can be received with this architecture. from nearly DC to 2 GHz. For future mobile communication standards, the frequency range has to deal with frequencies beyond 2 GHz up to 6 GHz. Nowadays IEEE802.11ac standard is located at 5GHz. Based on this concept a digital-analog converter is designed to deal with a higher bandwidth than other devices nowadays. The DAC is used in the transmission path of the design.

3.2. Idea of the Riemann Pump

The Riemann Pump, named after the mathematician Riemann, who founded the Riemann Integral, is a special charge pump. A charge pump as the name suggests pumps electrons into a capacitive load. Across the load capacitance a voltage is created. By adjusting the switches for up or down the voltage can be adjusted, as seen in Fig. 3.1.

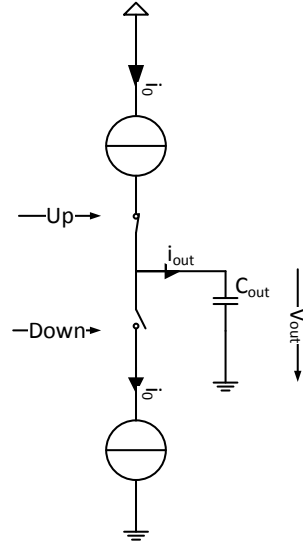


Fig. 3.1.: scheme of a charge pump; works like a Riemann Pump with one-bit resolution

$$V_{out} = \frac{1}{C_{out}} \int_0^T i_{out}(t) dt, \quad T = \frac{2 * OSR}{f_{sample}} \quad (3.1)$$

The Riemann Pump is a digital-to-analog converter based on the concept of a charge pump. A few charge pumps with different sized sources in parallel shows the concept of this fast digital to analog converter. With the ability to control the switches really fast, because of the use of GaN25 technology, which have a high transition frequency, a high bandwidth is reached.

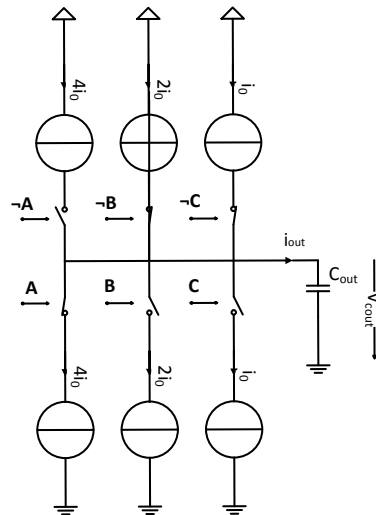


Fig. 3.2.: Concept of the Riemann Pump with three-bit resolution

The working principle is to integrate a current into a capacitive load, this integration is based on Riemann Integral, where the name come from. This integration converts

the current into a voltage. This output voltage can be applied to the input of a power amp and then to the antenna to propagate it. The current, which charges the capacitive input impedance of the power amp, is controlled by a digital code. A fixed set of slopes, represents the different current sources. A desired signal in the time-domain is generated with MatLab. This signal can consist of many different signals (different carriers and modulation types). This signal is sampled with the given set of slopes. The minimization of the error leads to the Riemann Code. With this Riemann Code (digital) the driver circuit is controlled. This leads to an analog signal formed by the digital input signal.

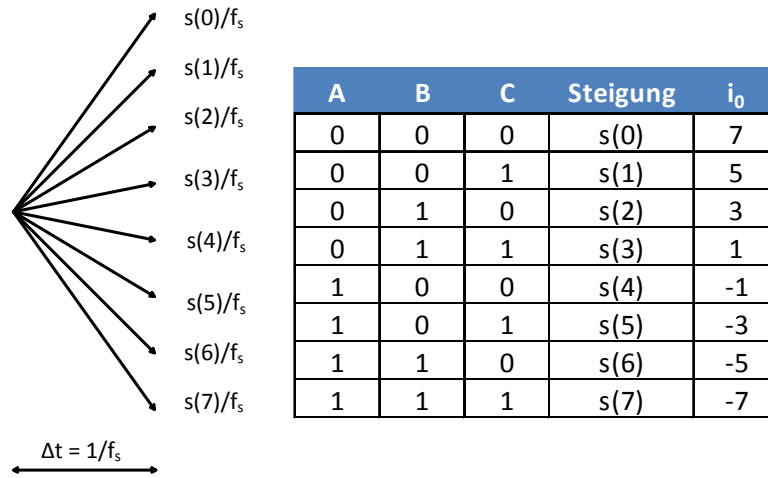


Fig. 3.3.: slopes and corresponding code of the synthesized signal

With this information a high speed digital to analog converter is created. In the following the Riemann Integral is shown.

This integral with its slopes as cited in 3.3 generates the riemann code which controls the switches of the circuit. This is done by minimizing the error between the theoretical, desired signal and its synthesized one as shown in Fig. 3.5 The signal to noise ratio is calculated in equation 3.2. Quantization noise model reference: analog device

$$\text{SNR [dB]} = 6.02N + 9.03r - 7.78 + 10 \log_{10} \left(1 - \frac{1}{2}^{N-1} + \frac{1}{2}^{2N} \right) \quad (3.2)$$

Description of the OSR, Nyquist-Shannon theorem and the SQNR... The OSR (over-sampling ratio) is four and hence due to the Nyquist-Shannon theorem, the sampling f (frequency) is eight times the signal frequency. This in mind, tuning the sampling frequency will result in tuning the signal frequency. *introducing noise due to the conversion* SQNR (Signal-to-quantization-noise-ratio) The deviation of the two signals is lying in the nature of converting digital to analog in form of quantization noise.

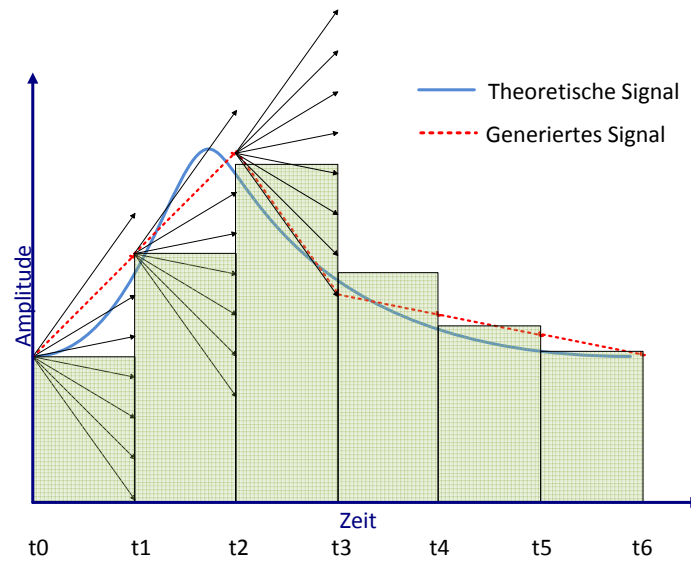


Fig. 3.4.: Integral of the current which pumps charges on to the cap.

3.3. Characteristics of high speed Digital-to-Analog converter

3.4. summary - evaluation

Evaluation of the idea. In the next chapters a proof of concept is done. What are the drawbacks, advantages and disadvantages.

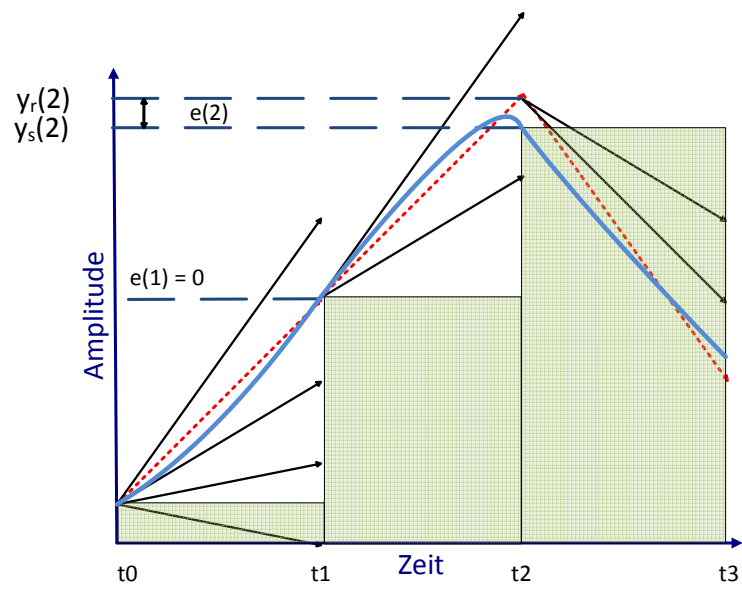


Fig. 3.5.: Code generation - error minimizing

4. Riemann Pump Circuit design

Description of the approach you have taken to solve the scientific or technical problem which you were posed. Outline the design, the methodology and overall structure of your experimental approach

After a literature survey on the topic of the Riemann Pump and the corresponding high speed DAC (digital-to-analog converter) an approach is chosen to implement which seems to fulfill the most of the characteristic parameters 3.3. This concept of push-pull stage seems to fit the best in a simple way with elements already used... -> verified, validated, tested, measured,... In addition to this parameters the realised approach is a first, easy to implement way to design such a complex system. Since the scope of the thesis is limited to time issues and there was no time for a stand alone design and redesign an already known concept of D. Maksimovic [1] is used.

The concept of the Riemann Pump as seen in Fig. 3.2 is realised with the design tool ADS (Advanced Design System). The first step was to design a A digitally controlled charge pump with eight different slopes is created, called Riemann Pump. To show that this pump is able to convert a digital signal into an analog one an example code is generated. As a MATLAB algorithm do not exists, which computes the Riemann Code, it is done by hand. In fact of the high energy consumption, the realized DAC is designed for the integration in a base station. Because it converts a digital bit sequence into an analog rf signal it is implemented in the transmitting path. Based on the idea of a push-pull stage the load impedance of the charge pump is designed first.

4.1. Approach and implementation of the Riemann Pump

One possible approach to design a charge pump as shown in Fig. 3.2 was with concept of a Push-Pull stage. The concept of the chosen push-pull stage had the advantage of an integrated driver circuit which allows to switch the high side transistor efficient. This concept is usually used for power electronics [-> which power electronic, refer to]. The first approach of designing a Riemann Pump was with a concept of a Push-Pull stage. This push-pull stage should charge a capacitive load at the output, which is the same as a normal charge pump. Push-pull stages complementary switch a high- and lowside transistor as in

a charge pump. This was one possible approach. Concept of Maksimovic.

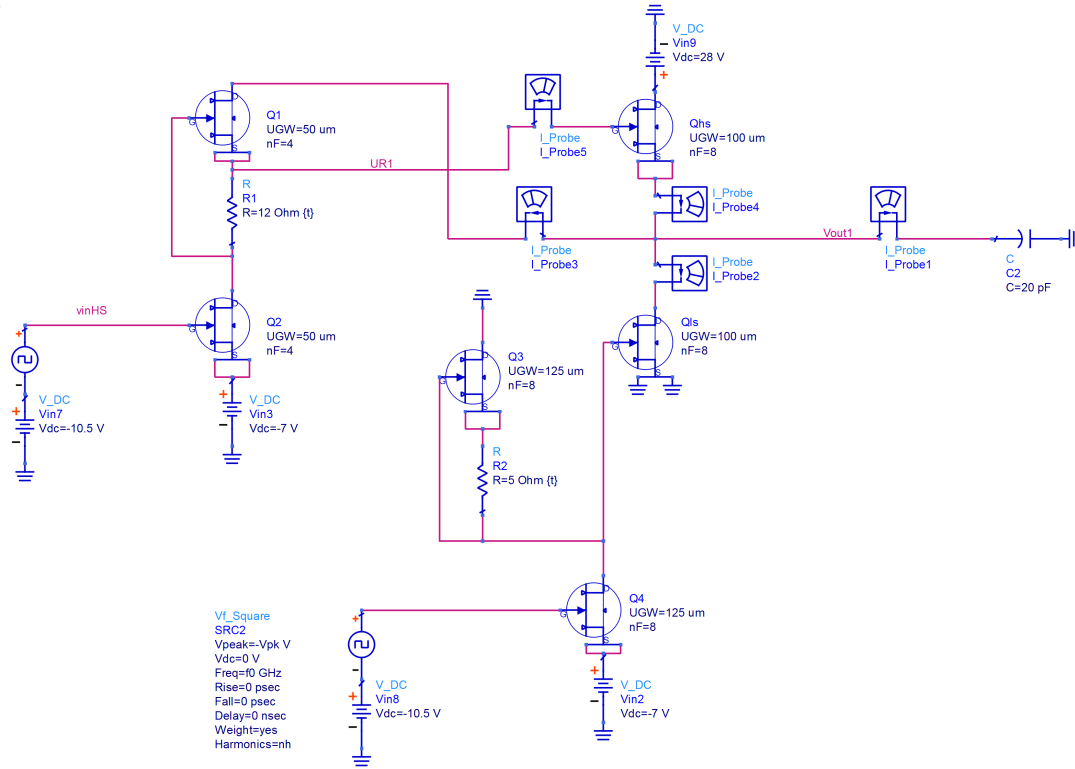


Fig. 4.1.: Schematic of a driver circuit with push-pull stage representing one bit of the DAC called Riemann Pump

4.2. Identification of the load impedance

To proof the concept of the chosen approach an appropriate output impedance was needed to synthesize the desired signal. The suitable output impedance was identified using the assumption to drive a power amplifier with the synthesized signal.

The advantage to drive a power amplifier with the synthesized signal would be... to synthesize a signal near to the RF- front end e.g. in a base station for mobile communication. - paper why this is needed As a 20 W power amplifier would be taken for the transmitting path of a base station the corresponding gate periphery of a GaN25 transistor would be 4 mm. This is a keep it small and simple approach to get a first idea of the concept. Otherwise a more accurate way would be to take a broadband power amplifier as load. The transistor model with this gate periphery was tuned due to the MAG (maximum available gain) to get the complex impedance of the power amplifier. After the tuning process a S-parameter simulation determined the input impedance of the power amplifier which corresponds to the load impedance of

the designed Riemann pump circuit. This transistor model HEMT (IAF_GE_MSL_A204/IAF_GaN25_HEMT_CS_LS_SHfull) used in ADS were modelled at the IAF.

The first assumption is that the load is a pre-power amplifier which generate a power of 20 W. To generate this power, the gate periphery of a GaN25 HEMT has to be 4 mm based on the approximation(- official reference???) $5 \frac{\text{W}}{\text{mm}}$. To get this gate periphery four transistor in parallel each with 8 finger and $125 \mu\text{m}$ are designed for the power amplifier. The bias point is determined with the MAG. Therefore the following load impedance could be determined.

$$Z = R - jX_c \quad (4.1)$$

With the help of the S_{11} parameter plotted in the smith chart Fig. 4.2 the load impedance can be determined. The load impedance got a capacitive reactance. The real part of the impedance is roughly $R = 1.89 \Omega$, while the imaginary part is capacitive. An important point is the input capacitance is increasing with frequency. While it is normal that the imaginary part of the impedance is increasing with frequency, the input capacitance is not.

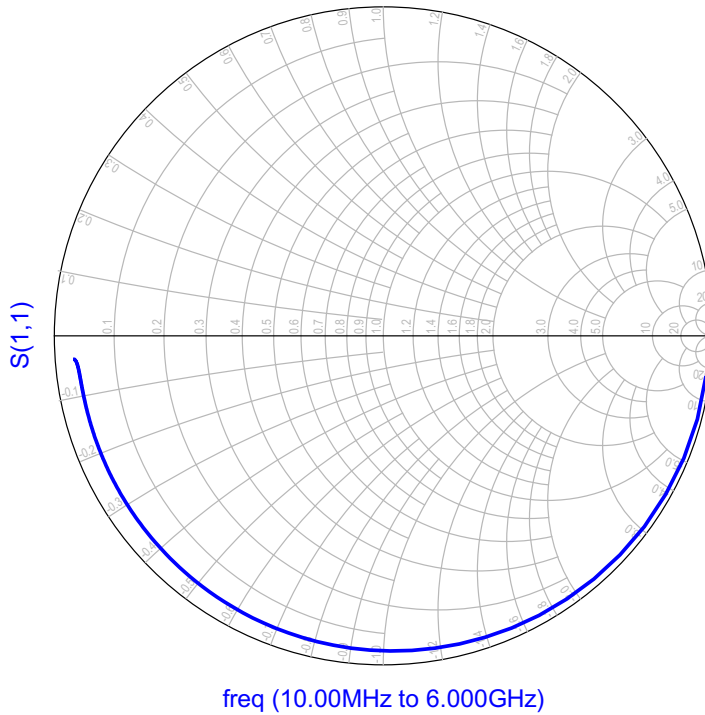


Fig. 4.2.: smith chart representing the load impedance

The load capacitance is calculated through the complex impedance:

$$C = \frac{1}{2\pi f X_c} \quad (4.2)$$

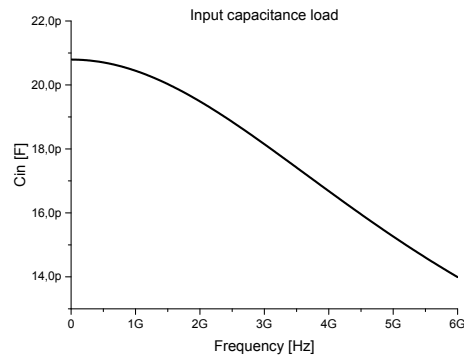


Fig. 4.3.: frequency dependent input capacitance of the load

4.3. Dimension of the used components

The transistor dimension were... Different for driver circuit and power circuit... resistor to reduce the energy consumption, for higher efficiency.

The approach of the push-pull stage Maksimovic, Maroldt.

Approach of theoretical and synthesized signal -> MatLab generation of Riemanncode, SNR.

Stability, driver concept, energy consumption, frequency bandwidth, gain Schematic design in Advanced Design System 2014. concept, ideas... **length of the bonds, number of bonds, thickness of bonds ask Dirk Meder. A lot of vias - more inductance - voltage drop between layers. short as possible lines, no rechtecke - para caps in the edge. first filter cap to supply pin near the chip. number and cap size determined on experience.**

Control voltage of 5 V realization with OPAMPS? Possible to overdrive opamps instead of using broadband ppa.

4.4. Circuit design summary and discussion

*Drawbacks, problems, challenges. Same realisation problems and difficulties: Problem of BANDWIDTH, Vpp of control signal (5V pp for GaN transistors), high side driver, no complementary transistors available in III-V technology, low loss driver, high speed driver, digital control driver, too high energy consumption (stability???) **bandwidth limitation** The lower bound is determined by the sampling time (inverse of the sampling frequency) and the smallest current achieved with the dimensioned transistors. The smallest achievable current times the smallest sampling time (highest sampling frequency) determine the smallest absolute slope achievable.*

Is every signal possible to create?→ a rect signal has too steep flanks to create. The signal bandwidth ranges from DC to 6 GHz but what is the amplitude range? Is there a limitation regarding the amplitude?

The smallest current is determined by the dimension of the transistor, which drives into saturation. The smallest saturated current is determined by the push-pull transistor geometry, here: 532 mA.

5. Circuit simulations for generating various waveform signals

The circuit simulations are run to validate the behaviour of the conceptual design of the Riemann Pump. The simulated output signal already identifies some fundamental ideas to understand the drawbacks and trade-offs of the designed circuit.

To investigate the theoretical concepts of chapter 4 the harmonic balance simulator is used. The harmonic balance simulation is done with the design tool ADS. The benefit of the harmonic balance simulation is that the whole system is modelled in a steady state mode, so that no transients influences the results. *"Harmonic balance is a frequency-domain analysis technique for simulating non linear circuits and systems[...]"* ADS_Harmonic_Balance.pdf

In a first step the analog signal across the output impedance in the time domain is plotted to check whether a signal could be synthesized or not. After various signals could be synthesized, a short stability and energy consumption analysis is done. The stability check is needed to validate that the circuit do not oscillate. As well the circuits energy consumption has to be checked if it is in a moderate range (*which is the moderate range? mention it here?*) since it could be implemented in mobile devices.

In the last step a simulation is run which makes the concept comparable to the realized circuit. In this simulation the transistor dimensions are adapted to the dimension of the built demonstrator. This should give an insight to the behaviour of the constructed demonstrator.

It is important to note that all simulations are done under ideal conditions and hence no losses are taken into account. The modelling and simulation of the designed circuit under real conditions considering all loss effects would go beyond the scope of this thesis. Therefore a keep it small and simple approach is chosen.

5.1. Generating various analog signals with digital input control

The generation of analog signals at the output of the designed circuit is the purpose of this concept. The designed Riemann Pump should be able to create various (arbitrary) waveform signals by converting a digital bit sequence into the analog output signal. Simulations in time domain are required to validate the signal integrity of the synthesized signals since the output signals consist of the integration of current over time to charge a capacitor at the output. If the output signal is verified to be as good as wanted, a simulation in the frequency domain can show the spurious free dynamic range of the DAC.

To synthesize a certain analog signal at the output the corresponding Riemann Code is needed. Due to the fact that no algorithm exists which computes this Riemann Code, it is done manually.

The presented DAC have a resolution of three bit and synthesizes signals with an OSR of four. The components used, are optimized with respect to the signal integrity. The dimension of the used components are tuned while simulation to ensure the desired output signal. In contrast to this optimized components, chapter 5.4 deals with the simulation done with real dimensions of the demonstrator components. This simulation should give an insight to what is expected for the measurements.

5.1.1. Sine wave generation in the time domain

As known from basic signal processing lecture [REF.?] the sine wave for continuous time is the elementary signal and therefore synthesized first. For the generation of this sine wave a corresponding Riemann Code is required which will be converted to the analog output signal.

This Riemann Code is generated by hand via an approximation of a sine wave with a sequence of eight different slopes. This eight different slopes represents a three bit resolution of the DAC while the sequence consists of eight sampling points which refer to the OSR of four.

Figure 5.1 presents the sequence of slopes used to approximate a sine wave.

This sequence of slopes, referred to i_0 values, is:

$$+7 \quad +3 \quad -3 \quad -7 \quad -7 \quad -3 \quad +3 \quad +7, \quad (5.1)$$

which represents the following Riemann code:

$$000 \quad 010 \quad 101 \quad 111 \quad 111 \quad 101 \quad 010 \quad 000. \quad (5.2)$$

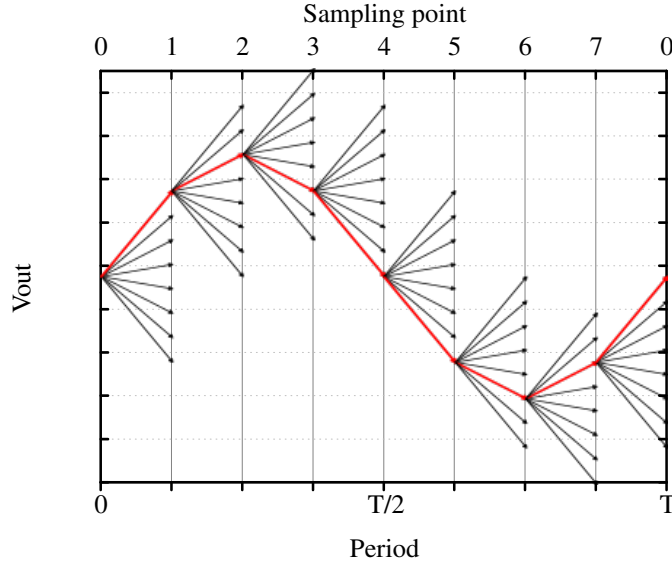


Fig. 5.1.: One possible approximation of sine wave generation to get the Riemann Code

The Riemann Code consists of eight triplets where each triplet represent the three different switches and the number of triplets represent the number of sampling points corresponding to the OSR. This particular generated Riemann code was used to synthesize sine waves in the frequency range between 500 MHz and 6 GHz, as seen in Figure 5.2.

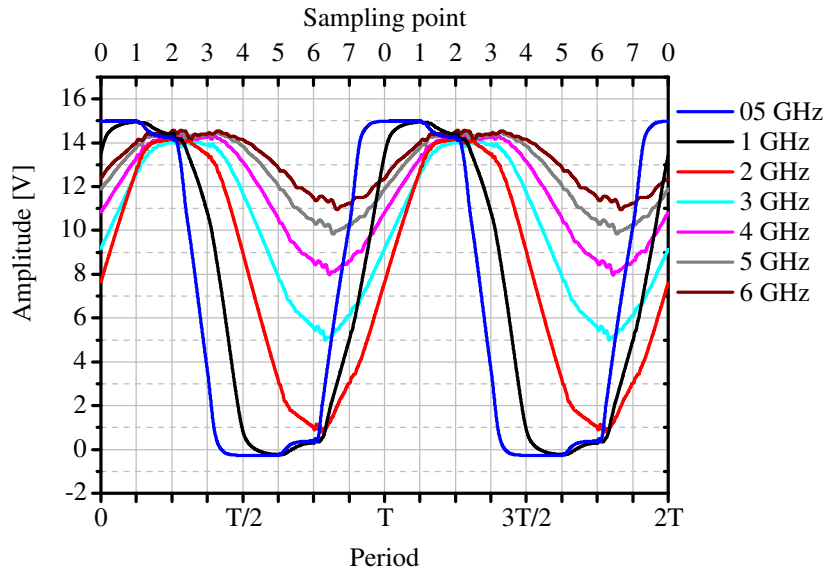


Fig. 5.2.: Synthesized signals with demonstrated Riemann Code for the frequency range of 0.5 GHz .. 6 GHz

The Figure 5.2 shows seven synthesized signals generated with the same input but with different sampling frequencies. Here the signals amplitude is plotted over two periods in time domain. Due to the different absolute sampling times, the amplitude of the signals

differ. The maximum reachable amplitude is the supply voltage, here set to 15 V to avoid unnecessary much heat and power losses. If this voltage is reached, the signal wave form is clipped and transforms the sine wave into an rectangular form. The shape from most of the plotted functions fit fairly to the one of a theoretical sine wave. But Figure 5.2 also highlights already some limitations of the designed circuit, as the blue curve turns into a rectangular signal form.

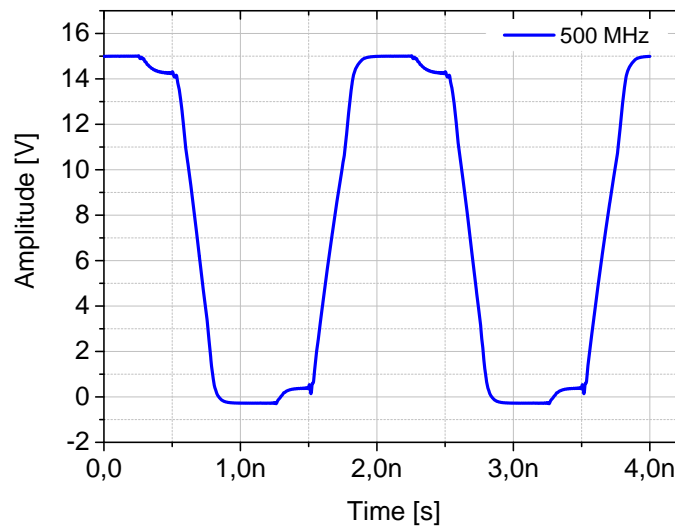


Fig. 5.3.: Synthesized sine wave for frequency of 0.5GHz

The circuit designed in chapter 4 is optimized to cover the frequency range from 1 GHz to 6 GHz fairly well, if a voltage swing of nearly two volts is still acceptable. If we go beneath a frequency of 1 GHz the desired shape of a sine wave is going to be rectangular due to the long sampling time, refer to Figure 5.3.

The blue signal which should represent a sine wave with a signal frequency of 500 MHz is clipped and hence shows the behaviour of a rectangular signal. This undesired behaviour is induced from a fully charged output capacitance. This signal frequency is the lower bound on the frequency range for the signals for the used configuration. The upper bound on the frequency range is the signal with the at least detectable voltage swing, which could be amplified. If at least a voltage swing of 2 V is accepted, in this configuration the upper bound would be a signal frequency of 6 GHz.

To show how accurate the generation of the signals is, figure 5.4 compares a theoretical sine wave signal (red) with a synthesized one (black) for a frequency of 1 GHz. The synthesized signal is same as the black curve in Figure 5.2. Setting up the right parameters,

a good fit to a sine wave can be performed.

In general the sine wave is of the form:

$$v(t) = V_{DC} + \hat{v} \cdot \sin(2\pi f \cdot t + \phi). \quad (5.3)$$

The synthesized signal (black) in Figure 5.4 fits pretty good to the theoretical sine wave, which has an amplitude of $\hat{v} = 7.5 \text{ V}$, a signal frequency of $f = 1 \text{ GHz}$, a phase shift of $\phi = \pi/4$ and an DC offset of $V_{DC} = 7.5 \text{ V}$.

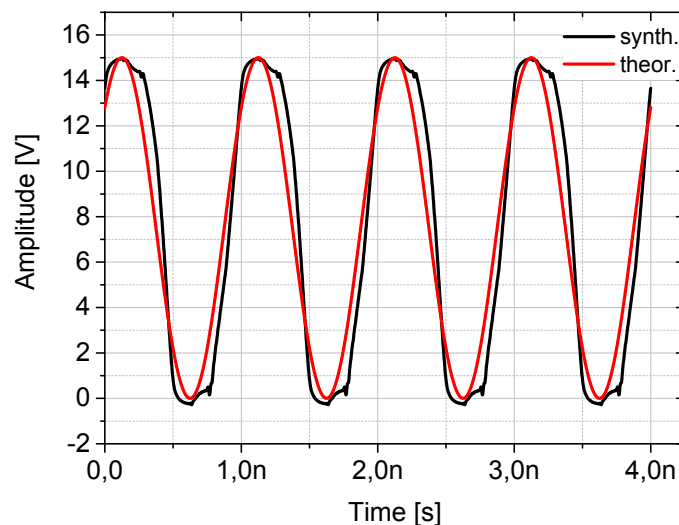


Fig. 5.4.: Synthesized sine wave with the theoretical sine wave

Although the fit seems to be very good, two distortions are visible in the peak and the valley of the synthesized signal. (\rightarrow Explaining these two distortions exactly for this signal frequency? Is it enough to explain some distortion at the example of 500MHz? \leftarrow) The fit is not perfect since the digital to analog conversion always introduce noise to the signal. (refer to chapter 3 and the SQNR).compare to the characteristic of DAC. Which SQNR is expected, which is achieved? \rightarrow plot?

Figure 5.5 highlights the difference between the synthesized and the theoretical sine wave form in a more detailed way.

A sine wave is compared to the synthesized one with their corresponding spectra. The spectra of signals are a lot easier to compare in contrast to the time domain signal with respect to the accuracy. Since the spectrum of a perfect sine wave only consists of a DC part and the harmonic frequency it is easy to check whether the generated signal fits to it or not.

On the top left side of Figure 5.5 the theoretical sine wave is plotted in red. Underneath of

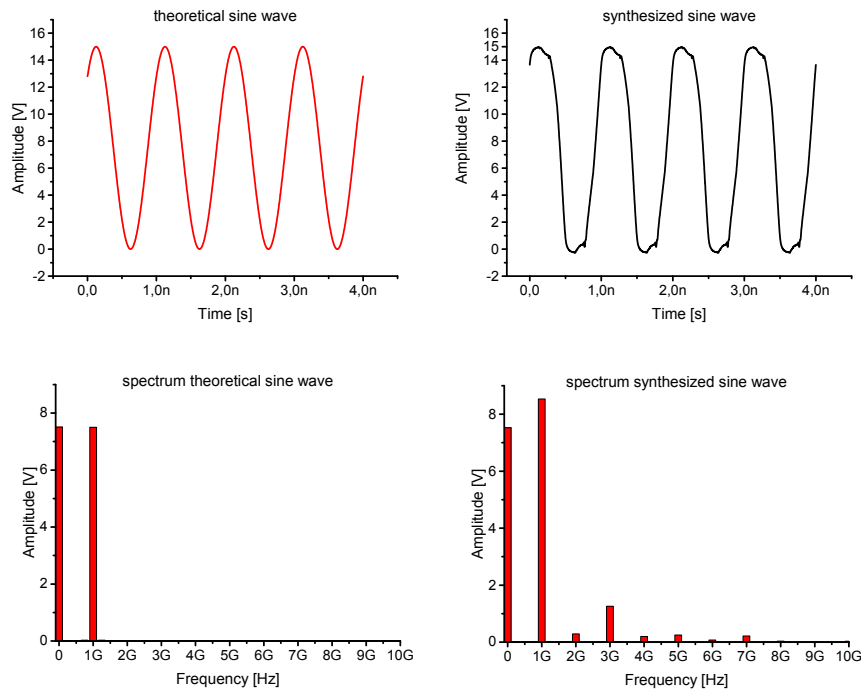


Fig. 5.5.: Comparison between a theoretical and a synthesized sine wave with their spectrum

(the time domain signal) its spectrum presents the frequency portion for the direct component at 0 Hz and a fundamental frequency portion at 1 GHz. This Fourier transformation represents the frequency portions of a clear sine wave. The synthesized sine wave on the top right side fits fairly well to the theoretical one. The spectrum of the synthesized signal shows nearly the same behaviour since only some harmonics distort the signal. Beside the direct component and the fundamental frequency component there are some additional unwanted frequency portions. The maximum absolute distortion of this synthesized signal is about 1 V in amplitude at the third harmonic at the frequency of 3 GHz. The 2nd to 10th harmonic are at most a half of a volt in absolute value of the amplitude (*relative reference?*).

The accuracy is very good. This can be verified by the signal to noise ratio -> explain, state the SNR

As the sampling frequency can be changed to tune the signal frequency of the output signal it is also possible to change the input control sequence to manipulate the shape of the signal. Due to the three bit resolution there is a limited number of different slope combinations to synthesize a sine wave. In fact there is the limit of six different combinations to synthesize the sine wave. The six combinations to synthesize a sine wave are: 75, 73, 71, 53, 51, 31 with respect to the i_0 values. The first digit indicates the slope of the first sampling point

and the second digit respectively the second sampling point for synthesizing the rising edge of a sine wave. These six combinations are plotted in Figure 5.6 over two periods for the signal frequency of 3 GHz.

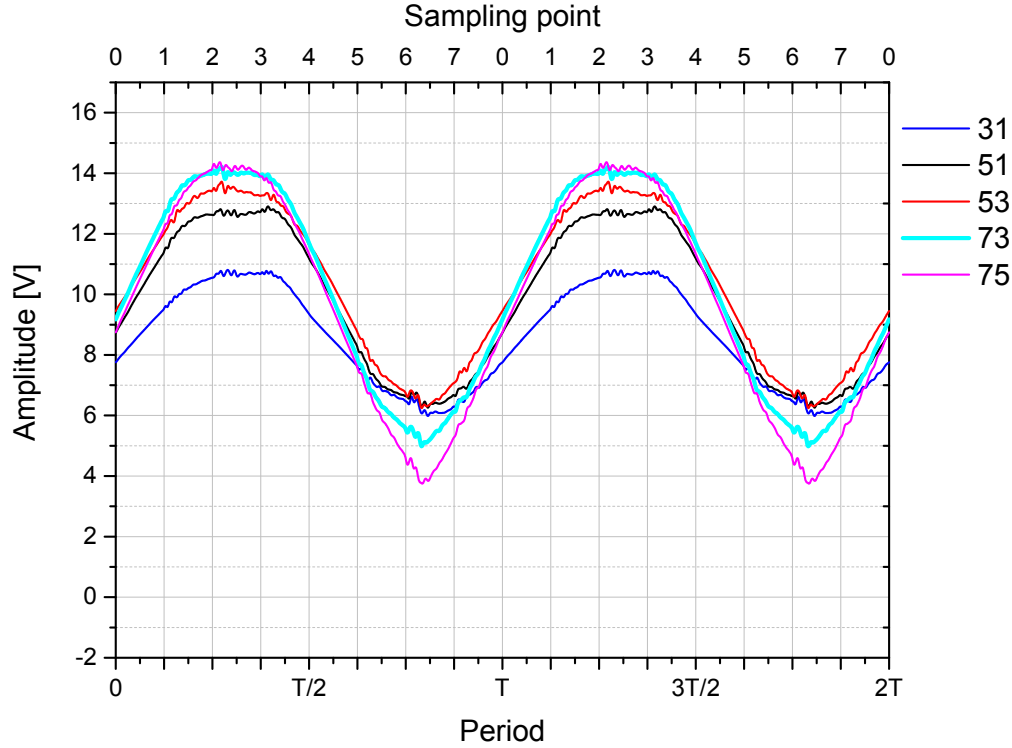


Fig. 5.6.: Signals with the same signal bandwidth but different input control

Figure 5.6 shows the different shapes of a sine wave for a frequency of 3 GHz. This is utilized to calculate the Riemann Code which fits best to the theoretical signal.

5.1.2. rectified sine wave generation in the time domain

Based on the same approximation principle of the signal in Figure ??, the Riemann Code for the rectified sine is generated. The chosen Riemann Code for the rectified sine is:

$$000 \ 010 \ 101 \ 111 \ 000 \ 010 \ 101 \ 111. \quad (5.4)$$

Using this code a rectified sine wave is synthesized by the designed circuit. The generation of the rectified sine wave is the same as for the normal sine wave. This only shows a different signal which could be synthesized.

5.1.3. triangular wave generation in the time domain

This is a triangular wave.

5.2. Stability analysis of the realised circuit

The stability and energy consumption analysis helps to get an impression/ understanding of figures and numbers of the designed circuit. Although this two aspect are of an important role for the development of a high speed DAC this analysis are not complete. The whole detailed analysis could not be investigated in this thesis due to complexity and time issues, what its meaning is not to belittle. For these aspects it is important to state that the designed circuit is in no way optimized with respect to those

The stability analysis is important to ensure that the circuit under test do not oscillate. To check this, the complex impedance at specific points in the circuit is measured. If the real part of the impedance is positive for the whole frequency range of the simulation, it indicates in an easy way that the circuit does not oscillate. This simulation is done within the ADS tool.

5.3. Energy consumption analysis of the realised circuit

If the OSR is increased to get a better accuracy, the switching frequency is also increased and therefore the energy consumption. In addition to the power consumption issue, the components have a unity current gain frequency limit. If the resolution is increased to get a better accuracy, the whole circuit would become more complex and the energy consumption would increase.

Using the OSR of four, we already get a sampling frequency of 2 GHz at the lower bound. For this reason the switches have to switch within 0.5 ns which increase the gate drive current which increase the power loss.

Due to the idea to use the presented topic for mobile communication it could be implemented in mobile devices, although this thesis only handles the device for the base station. If it could be used in a mobile device the energy consumption is critical.

The energy consumption of the designed circuit in chapter 4 is simulated with ADS.

There were the trade off between the power consumption of the high side switching transistor and the switching behaviour. Since the switching process needs to be very fast a high current is needed. This are losses. The driver circuit has to be optimized to reduce the

energy consumption while maintaining the the switching process correctly. If the correct hard

For the chips used for the demonstrator refer to the work of Stephan Maroldt who states, that the power consumption is: divided into static and dynamic ones. The switching losses are greater than the static ones. The losses are divided into dynamic losses of the switches and static losses.

5.4. Proof of concept simulation with existing components

This simulation is based on the measurements and the design of various chips from Stephan Maroldt. This two bit resolution simulation is done to compare the demonstrators measurements with the simulation. **two-bit resolution, osr = 4, keep it small and simple, frequency higher, demonstrator, assembly, less complex** The three bit resolution DAC was too complex to realize in a first approach on a hybrid substrate. Therefore an easier approach was designed to validate the proof of concept.

5.5. Evaluation of the simulation results for the Riemann Pump

Nonetheless the number of signals which can be synthesized with this particular concept is increased with the possibility to change to another combination of slopes to approximate the signal. All this calculation should be done with a signal processor and an algorithm. With the variation of the slopes and the variation of the sampling time in theory it is possible to create every single signal with more or less good SQNR.

When the component dimensions, like the switching transistors and load impedance, are fixed it is impossible to reach a bandwidth which goes from DC (direct current) to 6 GHz. The issue is that a small transistor dimension could synthesize signals to a very low signal frequency but will be unable to synthesize a signal at 6GHz due to the fact that the amplitude would be too small. Hence the signal frequency bandwidth would be shifted to the smaller frequencies. If the OSR is increased, the sampling time is decreased and therefore the signal quality is better because we have a more accurate synthesized signal. If the transistor dimension is chosen to be bigger, the higher signal frequency could be synthesized with a decent voltage swing but the low signal frequencies would turn into a rectangular shape. This is the trade off between the shift of the bandwidth (shifting to

even higher frequencies is possible but the bandwidth is nearly constant as long the output capacitance is constant too.) The trade off for the bandwidth shift to higher frequencies is, that with the signal frequency the switching frequency is increasing linearly (for an osr; eight times) and therefore the dynamic losses are increasing with this switching frequency. By the way the transistor switching speed is determined by the dimension of the driver circuit, so if the switching speed is increased the gate driving current has to be increased to switch the transistors.

The presented results show the theoretical feasibility of the approach. In a more enhanced project a MATLAB algorithm would compute this code by minimizing the deviation between a theoretical signal and the synthesized signal. evaluate the simulation results, what is to expect in realisation. What is the expectation to the measurement?

6. Realisation of a demonstrator

The realisation of the demonstrated concepts on a hybrid substrate was one goal of this thesis, to show its feasibility. To avoid building a too complex structure on a hybrid board the resolution of the DAC was restricted to two bit. Therefore a two layer substrate could be used to keep it small and simple. For the realisation two different versions of the demonstrator were designed. Both realisations were based on the former work from Stephan Maroldt who designed the chips.

6.1. Demonstrator using DDRI_X6 and DDRI_Y6 chips

A pad, which is surrounded by the conductive layer with its via holes, is used because the chips DDRIxy6 are connected to its metallized backside by through hole vias. In order to realize a Vdd supply voltage at the drain of this power mosfet and the output signal at the source, the chip does not be soldered onto the gnd layer of the substrate. Because otherwise the circuit would not work in a proper form. The schematic show that the output power transistor stage has to switch in a push-pull format. So the drain of the highside transistor is connected to Vdd which is realized with the chips on the rf pad. The lowside transistor and its driver circuit is the chip soldered on the substrate.

6.2. Demonstrator using DDRI_2C chips

In fact of that for this chips no backside connection to the chip backside exists, this chip can be directly soldered onto the substrate without losing the functionality. In contrast to the other version, here the gnd pads of the chip have to be bonded onto the substrate gnd. This version could be more convenient due to the better heat dissipation. The used chips:

1. DDRI_X6 and DDRI_Y6
2. DDRI_2C

were designed but unfortunately they do not have a simulation model which would make it easier to simulate the outcome.

The design and processing of a brand new mmic structure which contains the riemann

pump circuit was beyond the scope of this thesis, so it was a nice way to proof the concept to use the former designed chips. In addition to this MMIC chips some discrete components were used, e.g. bypass capacitors to filter out undesired distortion frequencies which could lead to oscillation which makes the circuit potentially instable/unstable.

In the realisation and layout progress many things must be considered.

The circuit is build on a hybrid assembly which combines the MMIC with the discrete SMD components on a Rogers 4003 substrate.

The input and output lines on the substrate were MSL (microstrip line) which were tuned to $50\ \Omega$. Tuned in this sense means, the lines were created with the right width, length and depth on the correct substrate with a special thickness. Important for the design of the input lines were that these lines are of same length due to phase angle issues for switching at the same time. The output line also was tuned to 50 ohm to guarantee a proper measurement with standard rf cables.

Also it would tried to get a proper distance between the lines to avoid any coupling.

An important thing was that the bond wires of in- and output lines to the MMIC (microwave monolithic integrated circuit) chips should be of the same length. The idea is that the high frequency digital signal are not allowed to have phase angles, because the switches have to switch all at the same time. Timing problems are expected to occur within the measurement.

In addition to this, the chips are producing power which produce a lot of heat and this heat has to dissipate. One important point is the heat dissipation. The chips have to dissipate the heat away form them. Here the different layouts comes into play. In a first version the chips (DDRi_XY6) are mounted on an island/pad and in the near of that a conducting layer with via holes are set to spread the heat over the air bridge (ambient temperature) to the via hole to the backside. This is not the optimal way to dissipate the heat, but the only to handle some heat dissipation. In a second version the other chips (DDRi_2C) which were not connected through via holes to the metallized backside of the chip, are soldered on the conducting substrate of the rogers hybrid substrate. This conductive layer have a lot of via holes to the cooled backside of the rogers substrate. The heat could spread directly from the backside of the chip which is metallized through the via holes of the substrate to the substrates backside. This second version could be the more efficient/convenient way. But the chips designed by S. Maroldt are a little bit older and therefore the taping of the wafer could be not as good as the newer ones. - what are other reason to not use this one? Due to this heat dissipation problem it would resign to package the chips into an QFN package

For bonding, the normal 25u Au bonds are used. The bonds length are given to the assembly limits for spacing of conducting layers of the manufacturer.

In- and output connectors are SMA jack connectors, to connect to standard RF cables. A few bypass capacitors are used based on the experience and experimental advice of some colleagues, rule of thumb. Suitable capacitors were those with a high ESR (equivalent series resistance) which means a bad q-factor, and of course the temperature range, the voltage range should be suitable to the purpose (flatten mag of imp vs. freq broadband good). (Bypassing and operating frequency not necessarily linked to each other. Bypassing a greater range than the potential operating frequency) (Culture Cargo principle). The first bypass capacitance the chip supply voltage sees is a MMIC cap directly assembled near to the supply pin of the chip.

Maybe the number of via holes on the substrate to the backside could create some additional inductance. keep that in mind for the measurement.

The dc supply slowly increase due to the fact of thermal issues. The V_{ss} is -5V and V_{dd} is 15V

Capacitive coupling could be a problem, through the dc supply lines to the input lines. What about the coupling from the substrate backside to the conducting layer of the substrate? What about inductive coupling via the via holes or so?? Other coupling?

The chips are different in order that the DDRi_2C chip is not connected via through hole via to the metallized backside of the chip. Therefore this chip can be soldered to the substrate, which has a lot of via holes for thermal dissipation, without loss of functionality.

- chip with gnd vias on island and nearby copper plate with thermal vias to cool down the ambient temp of the MMIC
- chip without gnd via, direct soldered on the copper with thermal vias

The two layouts were ordered at Contag in Berlin on 22nd Feb. The components needed to be ordered are ordered at digikey in the Netherlands.

7. Measurement results

The heart of the thesis, comprising a presentation of the functioning system and thus the culmination of the work. Important is an analysis of the results as well as a comparison with the state of the art. The reader should understand in this section why you should be awarded a MSc degree.

To demonstrate that the designed circuits really can synthesize a signal from a digital input signal, a time domain measurement would be necessary. To measure in time domain, an oscilloscope comes to mind. An important aspect is that the output impedance in chapter 4 is calculated but not assembled. The concept is based on the fact, that this circuit is pumping charges onto a output capacitance. This output capacitance should be the input of a power amplifier as a GAN transistor. Due to the fact that no power amplifier is connected to the output, the question comes to mind how to measure the output if no capacitance is connected to it with the oscilloscope. A first try is to show the push-pull of the supply voltage. This only would demonstrate the one bit switching but it would show that if a one bit switch is functioning properly, two or three bit are not as far as assumed. The second try would be to connect it to an active load pull measurement, but here the drawback is the limited harmonic control and that the input signal is limited in frequency and steepnes. As we want to digital control the circuit, a rectangular signal is needed. As we want a signal frequency of 100 MHz, an input frequency of at least 800 MHz is required.

7.1. Measurement setup

An overview of the measurement setup is given. The DC supply is the same for both measurement setups. The input control is depending on the system which is used for the measurement.

First option would be to scope a real time output (on-wafer) with an oscilloscope. For the output signal measurement in time domain with the oscilloscope the digital input signal is delivered from a high speed AWG. The digital input is generated from the AWG, amplified by an preamplifier to get a voltage swing of 5Vpp and at last a dc bias tee is connected to ensure the correct dc offset to the input. The input is controlled by an AWG from Keysight, programmed with a determined data set of bits. The key components are listed here:

- Keysight AWG - (1V := 0dB; 0.7V := -3dB)
- Broadband (35kHz-40GHz) amplifier (17dB gain) (digital signal with clk 1GHz, 10 harmonics -> 10GHz)
- Bias Tees (DC bias)
- DC supply (driver network, power transistor)
- DUT
- LOAD - OUTPUT ???

Secondly the output measurement with (Anteverta) active load pull system is done. For this measurement no AWG is needed to provide the digital input signal, since the measurement is done with a Anteverta active load pull system, this device is providing the input signal. In fact of knowing its input and output signal this device is capable to tune the impedance at arbitrary points in the circuit. This is a nice way to simulate a capacitive load at the output to show the behaviour of the circuit with this load impedance calculated in 4. By using this active load pull system, we have to reduce the number of bits for the resolution to one bit due to the fact, that the system only provide the option to handle four harmonics. We already use two harmonics for the differential input signal and one harmonic for the output tuning the impedance. Hence there is only one harmonic left for which no other input can controlled since two signals are necessary to get a differential input signal.

7.2. Measurement results/ Proof of concept /

Discussion of measurement results

In a first step it is to show that the designed circuit converts a digital signal to an analog one. It would be nice to see any effect corresponding to the digital to analogue conversion. *is it possible to measure the heat spreading on the substrate?* Is the measurement result expected due to the simulation? Can the demonstrator be simulated although no model for this chips exists? The real simulation are not done due to the fact that no losses respected.

8. Conclusions and outlook

A summary of the most important results, whereby a repeated emphasis of their relevance, importance and novelty cannot hurt. A brief precis of the envisaged future potential of the work is suitable here, but avoid addressing the Nobel Committee directly. The calculation of the Riemann Code have to be done with an external signal processor, which has to compute this code in real time. This could be a problem, since the energy consumption could increase and the real time calculation.

Bibliography

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Appendix

A. Schematic of the Riemann Pump circuit

B. Layout of the whole Riemann Pump circuit

bla bla bla bal bla lbal blalsl

bla bla bla bal bla lbal blalsl

C. Photography of the realized Demonstrator version 1

bla bla bla bal bla lbal blalsl

D. Photography of the realized Demonstrator version 2

bla bla bla bal bla lbal blalsl

